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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.
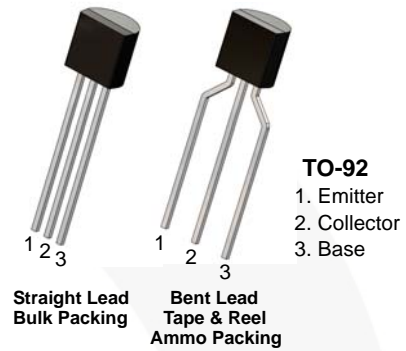
June 2016

BC638
PNP Epitaxial Silicon Transistor

Features

- Switching and Amplifier Applications
- Complement to BC637

TO-92
1. Emitter
2. Collector
3. Base

Straight Lead
Bulk Packing

Bent Lead
Tape & Reel
Ammo Packing

Ordering Information

Part Number	Top Mark	Package	Packing Method
BC638TA	BC638	TO-92 3L	Ammo

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25°C$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CER}	Collector-Emitter Voltage at $R_{BE} = 1\ K\Omega$	-60	V
V_{CES}	Collector-Emitter Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-1	A
I_{CP}	Peak Collector Current	-1.5	A
I_B	Base Current	-100	mA
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	-65 to 150	°C

Thermal Characteristics[1]

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Value	Unit
P_D	Power Dissipation	1	W
	Derate Above 25°C	8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	125	°C/W

Note:

1. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

Electrical Characteristics

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C = -10 mA, I_B = 0	-60			V
I_{CBO}	Collector Cut-Off Current	V_{CB} = -30 V, I_E = 0			-0.1	μA
I_{EBO}	Emitter Cut-Off Current	V_{EB} = -5 V, I_C = 0			-10	μA
h_{FE1}		V_{CE} = -2 V, I_C = -5 mA	25			
h_{FE2}	DC Current Gain	V_{CE} = -2 V, I_C = -150 mA	40		160	
h_{FE3}		V_{CE} = -2 V, I_C = -500 mA	25			
V_{CE}(sat)	Collector-Emitter Saturation Voltage	I_C = -500 mA, I_B = -50 mA			-0.5	V
V_{BE}(on)	Base-Emitter On Voltage	V_{CE} = -2 V, I_C = -500 mA			-1	V
f_T	Current Gain Bandwidth Product	V_{CE} = -5 V, I_C = -10 mA, f = 50 MHz		100		MHz

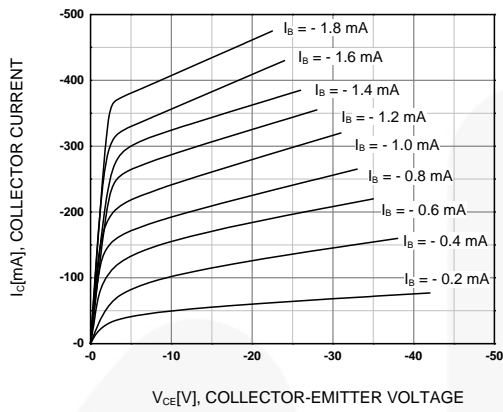# Typical Performance Characteristics

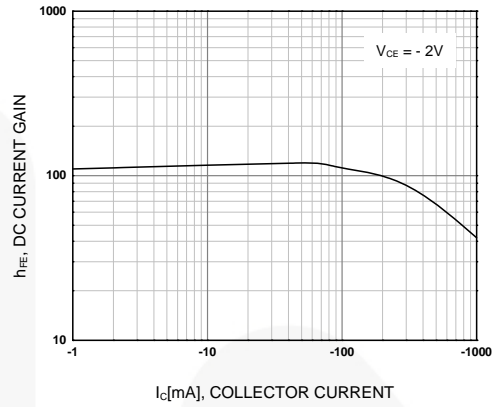**Figure 1. Static Characteristic**
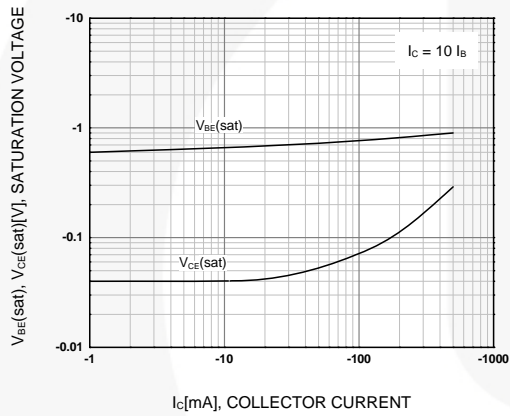

Figure 2. DC Current Gain
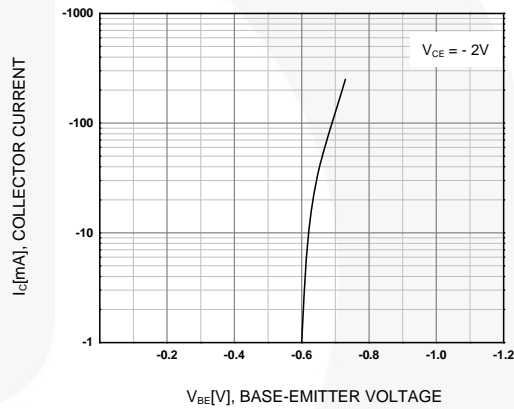

Figure 3. Base-Emitter Saturation Voltage and Collector-Emitter Saturation Voltage
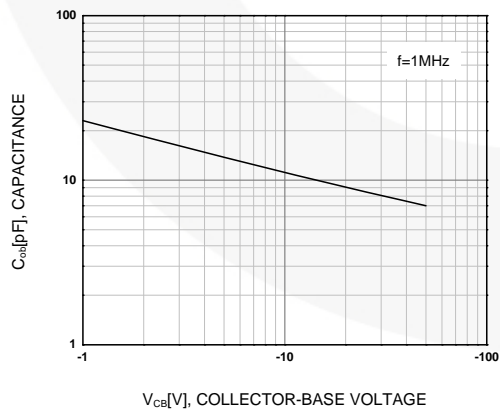

Figure 4. Base-Emitter On Voltage

Figure 5. Collector Output Capacitance
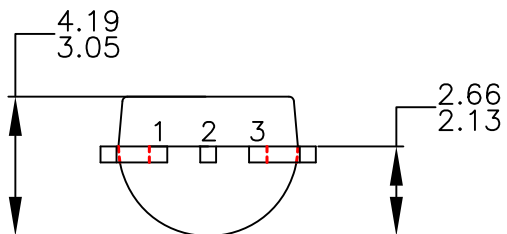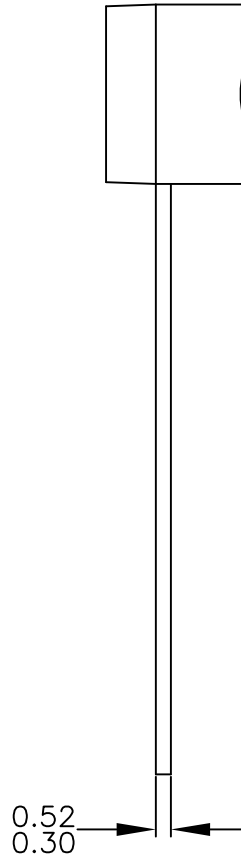
5.20
4.32

5.33
4.32

3.44
2.54

13.00
10.50

1   2   3

0.56
0.36

2.80
2.40

0.52
0.30

4.19
3.05

1   2   3

2.66
2.13
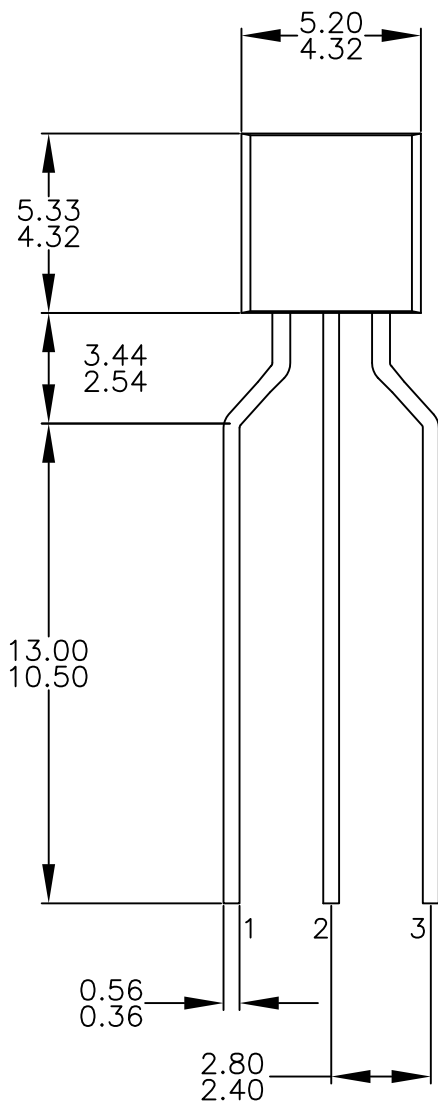
NOTES: UNLESS OTHERWISE SPECIFIED

A.   DRAWING CONFORMS TO JEDEC MS-013,
      VARIATION AC.
B.   ALL DIMENSIONS ARE IN MILLIMETERS.
C.   DRAWING CONFORMS TO ASME Y14.5M-2009.
D.   DRAWING FILENAME: MKT-ZA03FREV3.
E.   FAIRCHILD SEMICONDUCTOR.

PUBLICATION ORDERING INFORMATION

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